

FEATURES

- 10μs Short Circuit Withstand
- High Thermal Cycling Capability
- Non Punch Through Silicon
- Isolated AlSiC Base with AlN Substrates
- Lead Free construction

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Drives

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The 800DDM17 is a dual switch 1700V, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10μs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

800DDM17

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}	1700V
$V_{CE(sat)}$ * (typ)	2.7 V
I_C (max)	800A
$I_{C(PK)}$ (max)	1600A

* Measured at the power busbars, not the auxiliary terminals

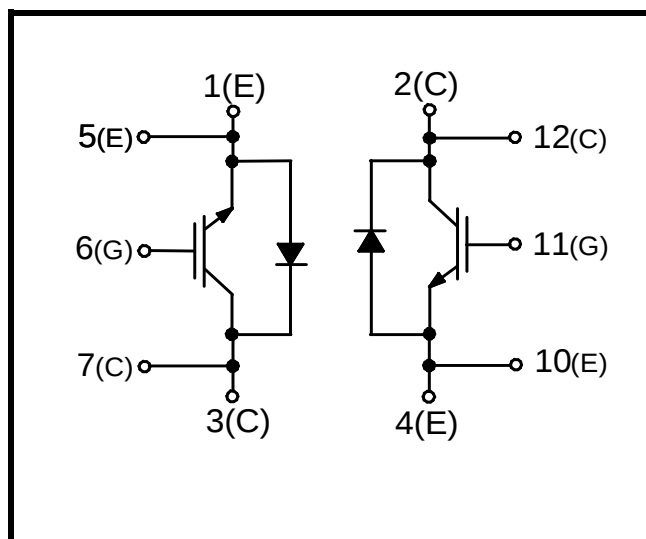
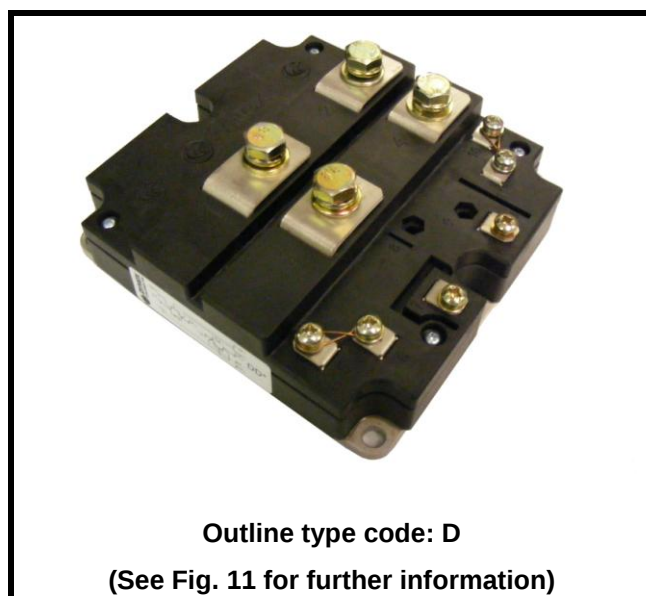


Fig. 1 Circuit configuration



Outline type code: D

(See Fig. 11 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{GE} = 0\text{V}$	1700	V
V_{GES}	Gate-emitter voltage		± 20	V
I_C	Continuous collector current	$T_{case} = 75^{\circ}\text{C}$	800	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 110^{\circ}\text{C}$	1600	A
P_{max}	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$	6940	W
I^2t	Diode I^2t value	$V_R = 0$, $t_p = 10\text{ms}$, $T_j = 125^{\circ}\text{C}$	120	kA^2s
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	4000	V
Q_{PD}	Partial discharge – per module	IEC1287, $V_1 = 1800\text{V}$, $V_2 = 1300\text{V}$, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material:	AlN
Baseplate material:	AlSiC
Creepage distance:	20mm
Clearance:	10mm
CTI (Comparative Tracking Index):	350

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor (per switch)	Continuous dissipation - junction to case		-	18	$^{\circ}\text{C}/\text{kW}$
$R_{th(j-c)}$	Thermal resistance – diode (per switch)	Continuous dissipation - junction to case		-	40	$^{\circ}\text{C}/\text{kW}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)		-	8	$^{\circ}\text{C}/\text{kW}$
T_j	Junction temperature	Transistor	-	-	150	$^{\circ}\text{C}$
		Diode	-	-	125	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-	-40	-	125	$^{\circ}\text{C}$
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

ELECTRICAL CHARACTERISTICS

$T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{CES}	Collector cut-off current	$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = V_{\text{CES}}$			1	mA
		$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = V_{\text{CES}}, T_{\text{case}} = 125^{\circ}\text{C}$			25	mA
I_{GES}	Gate leakage current	$V_{\text{GE}} = \pm 20\text{V}, V_{\text{CE}} = 0\text{V}$			4	μA
$V_{\text{GE(TH)}}$	Gate threshold voltage	$I_{\text{C}} = 40\text{mA}, V_{\text{GE}} = V_{\text{CE}}$	4.5	5.5	6.5	V
$V_{\text{CE(sat)}}^{\dagger}$	Collector-emitter saturation voltage	$V_{\text{GE}} = 15\text{V}, I_{\text{C}} = 800\text{A}$		2.7	3.2	V
		$V_{\text{GE}} = 15\text{V}, I_{\text{C}} = 800\text{A}, T_{\text{J}} = 125^{\circ}\text{C}$		3.4	4.0	V
I_{F}	Diode forward current	DC			800	A
I_{FM}	Diode maximum forward current	$t_{\text{p}} = 1\text{ms}$			1600	A
$V_{\text{F}}^{\dagger}$	Diode forward voltage	$I_{\text{F}} = 800\text{A}$		2.2	2.5	V
		$I_{\text{F}} = 800\text{A}, T_{\text{J}} = 125^{\circ}\text{C}$		2.3	2.6	V
C_{ies}	Input capacitance	$V_{\text{CE}} = 25\text{V}, V_{\text{GE}} = 0\text{V}, f = 1\text{MHz}$		60		nF
Q_{g}	Gate charge	$\pm 15\text{V}$		9		μC
C_{res}	Reverse transfer capacitance	$V_{\text{CE}} = 25\text{V}, V_{\text{GE}} = 0\text{V}, f = 1\text{MHz}$		-		nF
L_{M}	Module inductance – per switch	-		20		nH
R_{INT}	Internal transistor resistance – per switch	-		270		$\mu\Omega$
SC_{Data}	Short circuit current, I_{SC}	$T_{\text{J}} = 125^{\circ}\text{C}, V_{\text{CC}} = 1000\text{V}$ $t_{\text{p}} \leq 10\mu\text{s}, V_{\text{GE}} \leq 15\text{V}$ $V_{\text{CE(max)}} = V_{\text{CES}} - L^* \times dI/dt$ IEC 60747-9	I_1	3700		A
			I_2	3200		A

Note:

† Measured at the power busbars, not the auxiliary terminals

* L is the circuit inductance + L_{M}

ELECTRICAL CHARACTERISTICS

 $T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 800\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 900\text{V}$ $R_{G(\text{ON})} = 2.2\Omega$ $R_{G(\text{OFF})} = 2.2\Omega$ $L_S \sim 100\text{nH}$		1250		ns
t_f	Fall time			170		ns
E_{OFF}	Turn-off energy loss			230		mJ
$t_{d(\text{on})}$	Turn-on delay time			250		ns
t_r	Rise time			250		ns
E_{ON}	Turn-on energy loss			220		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 800\text{A}$ $V_{CE} = 900\text{V}$ $di_F/dt = 4000\text{A}/\mu\text{s}$		200		μC
I_{rr}	Diode reverse recovery current			460		A
E_{rec}	Diode reverse recovery energy			130		mJ

 $T_{\text{case}} = 125^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 800\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 900\text{V}$ $R_{G(\text{ON})} = 2.2\Omega$ $R_{G(\text{OFF})} = 2.2\Omega$ $L_S \sim 100\text{nH}$		1500		ns
t_f	Fall time			200		ns
E_{OFF}	Turn-off energy loss			360		mJ
$t_{d(\text{on})}$	Turn-on delay time			400		ns
t_r	Rise time			250		ns
E_{ON}	Turn-on energy loss			340		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 800\text{A}$ $V_{CE} = 900\text{V}$ $di_F/dt = 4000\text{A}/\mu\text{s}$		330		μC
I_{rr}	Diode reverse recovery current			530		A
E_{rec}	Diode reverse recovery energy			200		mJ

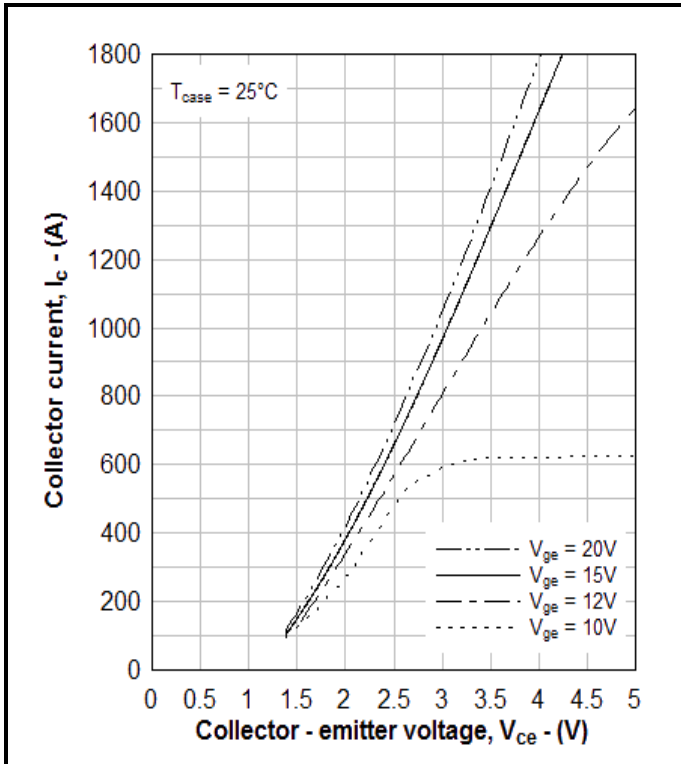


Fig. 3 Typical output characteristics

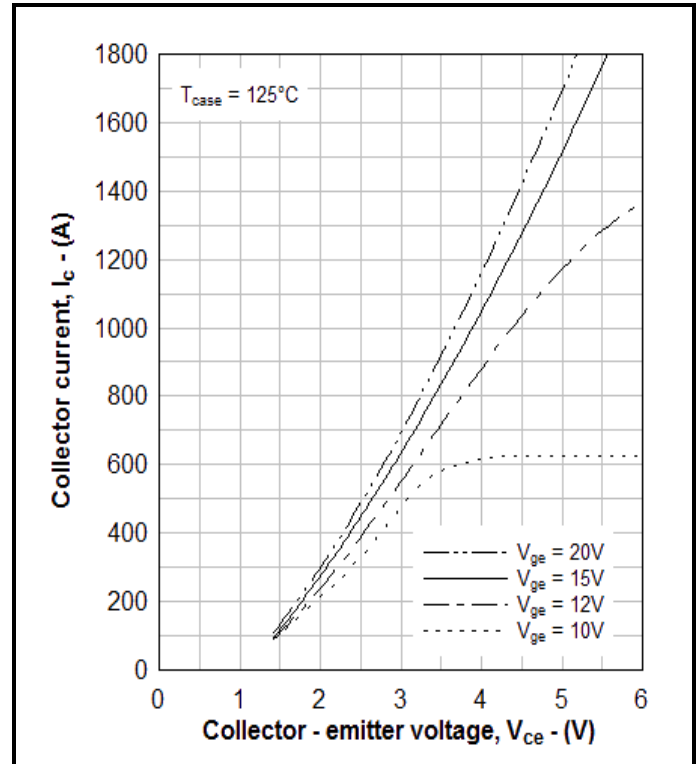


Fig. 4 Typical output characteristics

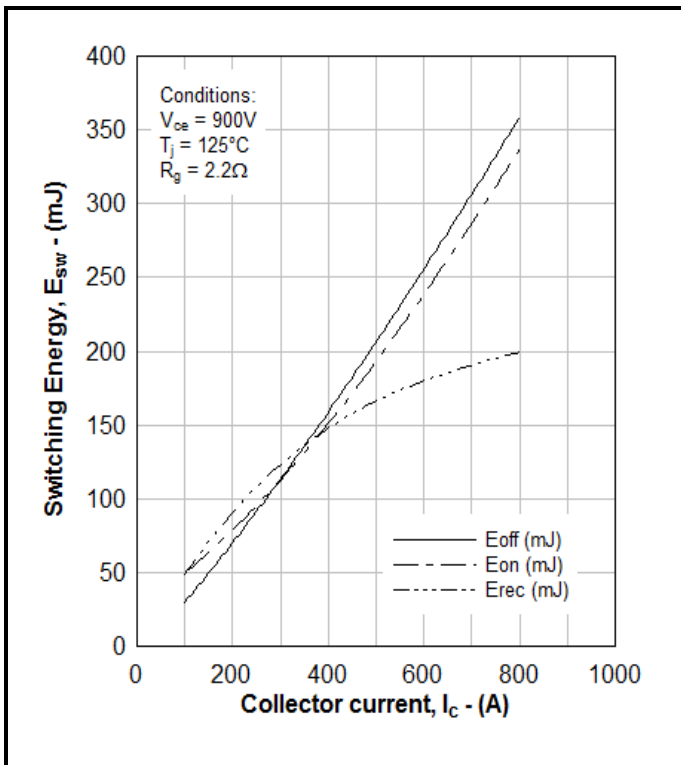


Fig. 5 Typical switching energy vs collector current

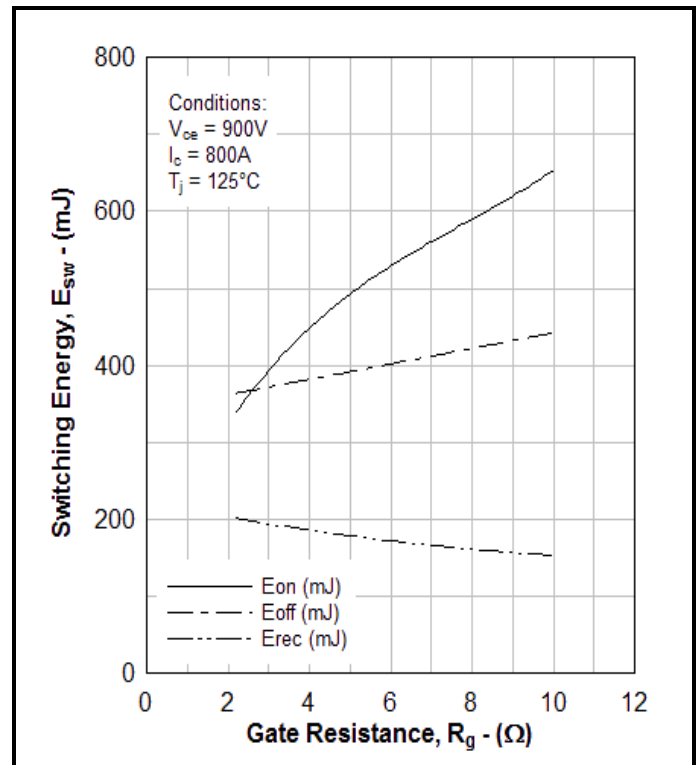


Fig. 6 Typical switching energy vs gate resistance

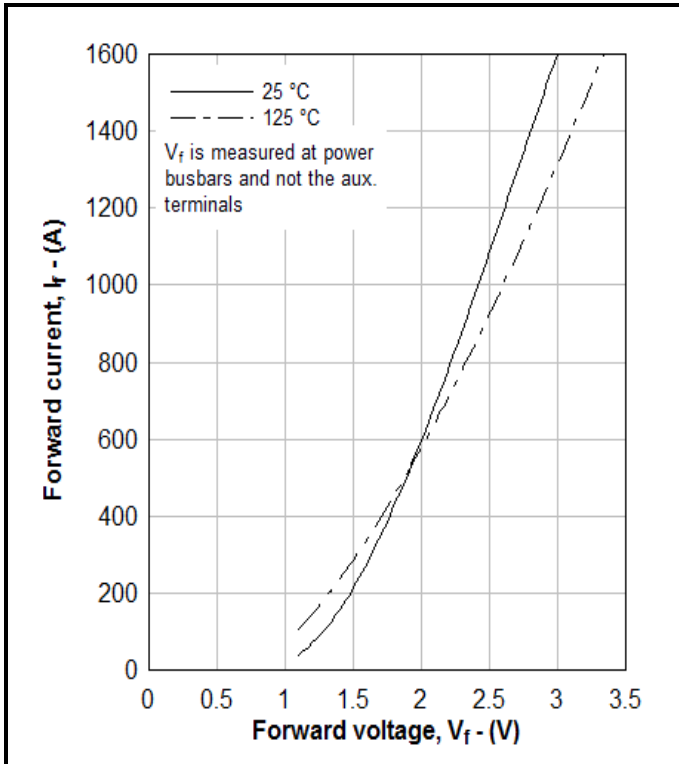


Fig. 7 Diode typical forward characteristics

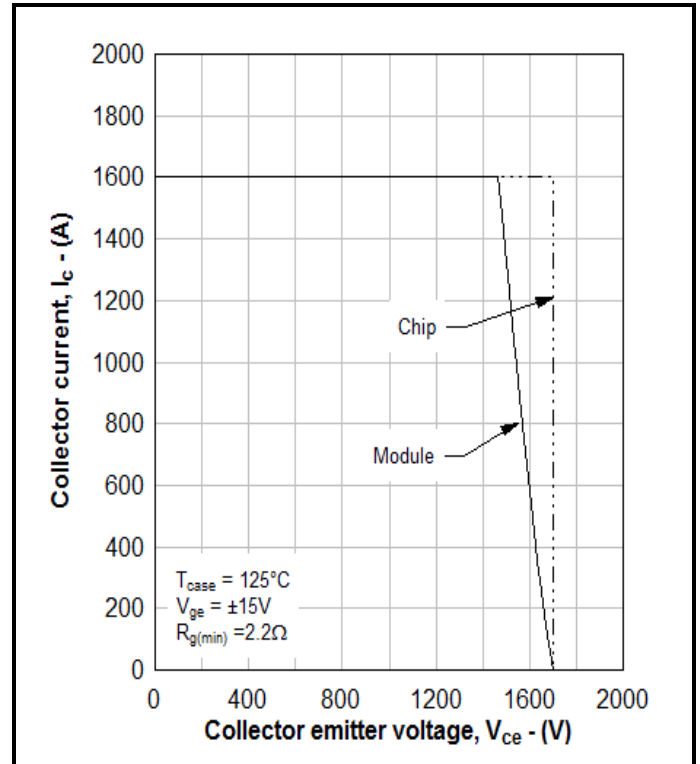


Fig. 8 Reverse bias safe operating area

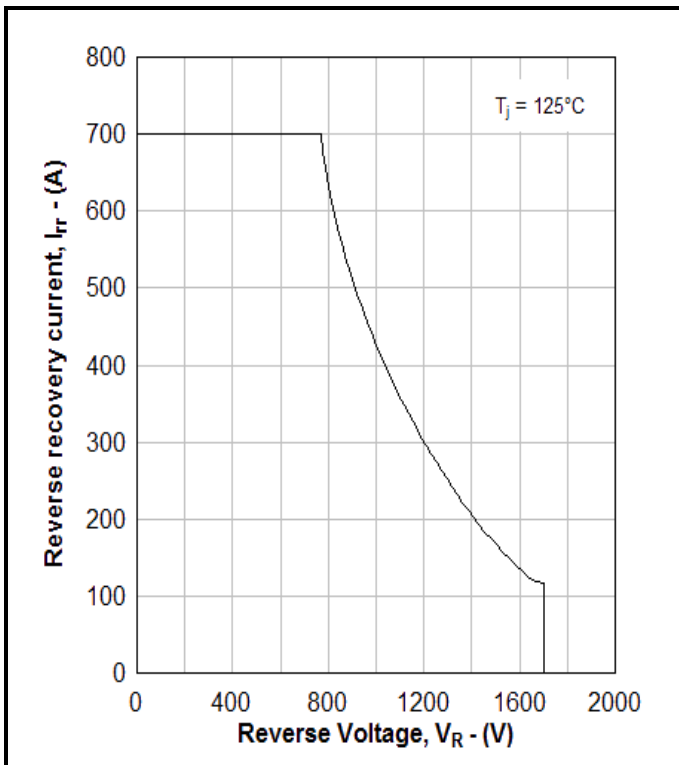


Fig. 9 Diode reverse bias safe operating area

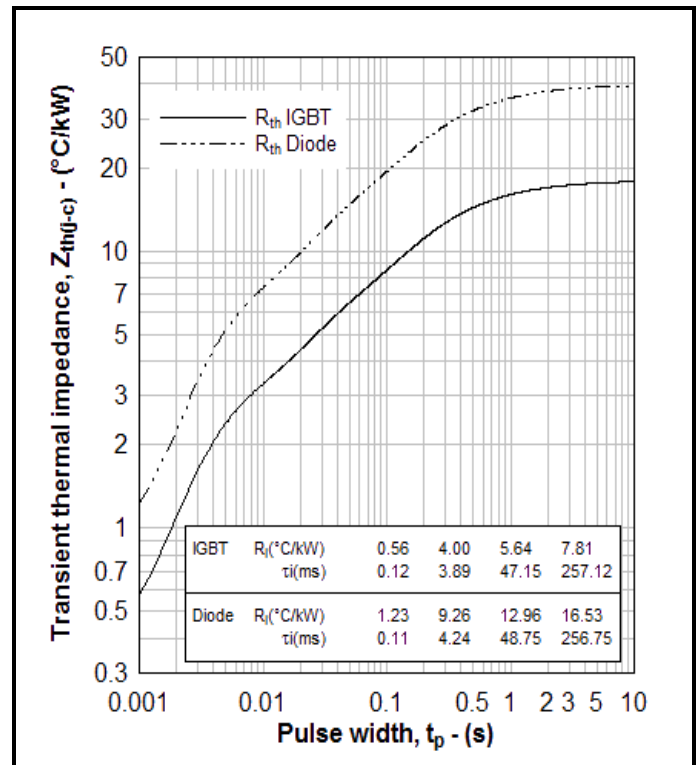


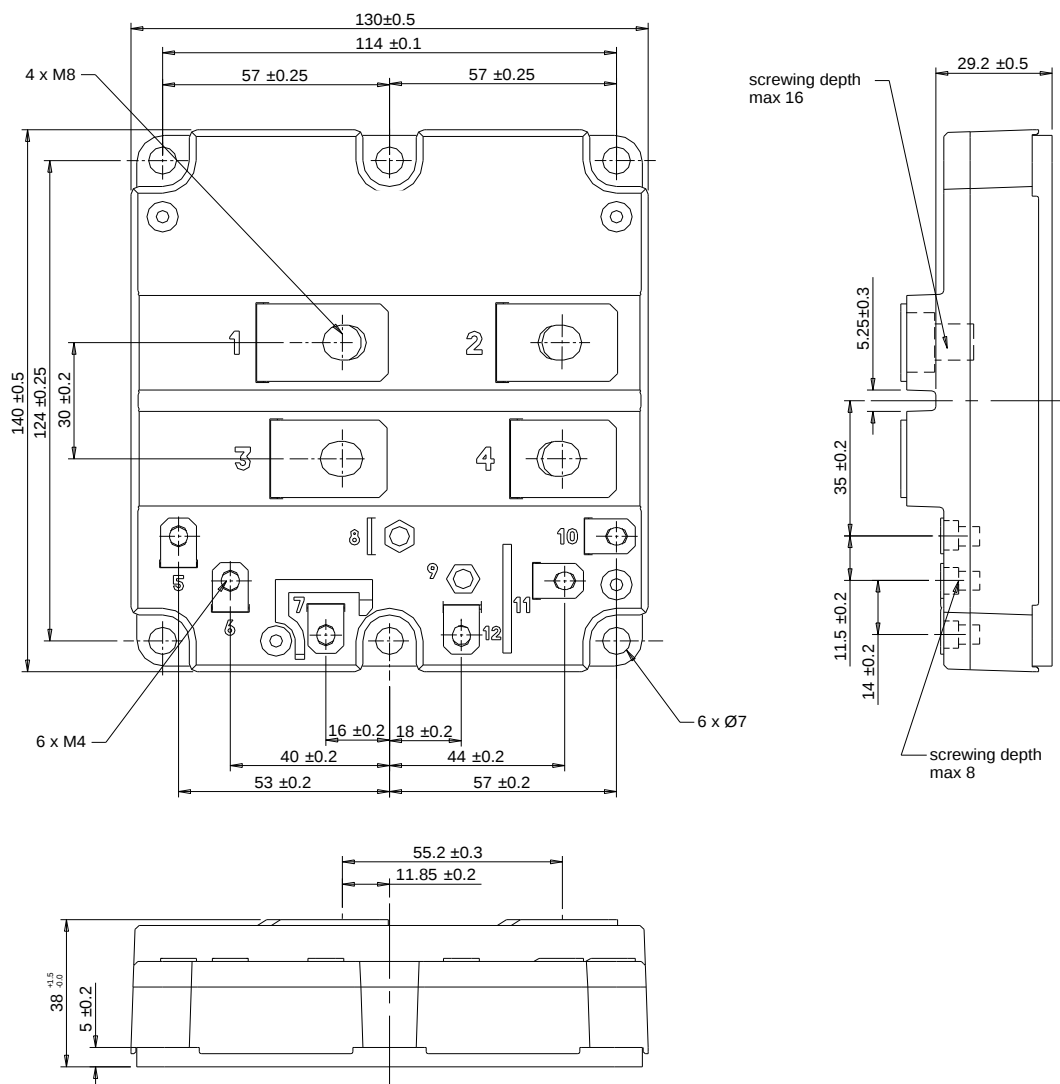
Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE.



Nominal Weight: 900g

Module Outline Type Code: D

Fig. 11 Module outline drawing